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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

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| APPL NUM 10024475 | FILING DATE 12/21/2001 | CLASS 285 | SUBCLASS - 3-1 | GAU 2811 | EXAMINER Im |
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****APPLICANTS:** Park Chan-ho;

****CONTINUING DATA VERIFIED:**

**** FOREIGN APPLICATIONS VERIFIED:**
REPUBLIC OF KOREA 01-2166 01/15/2001

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|--|---|----------------------------------|
| PG-PUB | DO NOT PUBLISH <input type="checkbox"/> | RESCIND <input type="checkbox"/> |
| Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no | | ATTORNEY DOCKET NO |
| 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no | | 1751-294 |
| Verified and Acknowledged Examiners's initials | | |
| TITLE : High voltage semiconductor device having high breakdown voltage and method of fabricating the same | | |

U.S. DEPT. OF COMM. PAT. & TM. PTO-436L/Rev. 12-94

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|---|-----------|---------------------------|------------------------|
| NOTICE OF ALLOWANCE MAILED | | CLAIMS ALLOWED | |
| | | Total Claims | Print Claim for O.G. |
| ISSUE FEE | | DRAWING | |
| Amount Due | Date Paid | Sheets Drwg. | Figs. Drwg. Print Fig. |
| | | | |
| <input type="checkbox"/> TERMINAL DISCLAIMER | | Application Examiner | |
| | | PREPARED FOR ISSUE | |
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